

CORRECTION

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Correction: Gate-tunable interfacial properties of in-plane ML MX₂ 1T'–2H heterojunctions

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Correction for 'Gate-tunable interfacial properties of in-plane ML MX₂ 1T'–2H heterojunctions' by Shiqi Liu *et al.*, *J. Mater. Chem. C*, 2018, DOI: 10.1039/c8tc01106k.

The authors regret that an incorrect description was used in the computational details section. The sentence "A periodic type, a Neumann type and a Dirichlet type boundary condition are used in the *x*, *y* and *z* directions of the device (Fig. 4), respectively." should read "A Neumann type, a Periodic type and a Dirichlet type boundary condition are used in the *x*, *y* and *z* directions of the device (Fig. 4), respectively."

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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